

N-type-M10(182.2×182.2*247) A



Monocrystalline Wafer

Comprehensive system certification

ISO9001:2022

ISO14001:2022

ISO45001:2022

Gokin

Key parameters

The file version202406

Conductivity type	N-type	PN testing machine
Dopant	Phos.(磷)	/
Resistivity/ Ω -cm	0.6-1.6	Wafer inspection system
Lifetime/ μ s	≥ 800	BCT-400
Oxygen concentration/ppma	≤ 12	FTIR (ASTM F121-83)
Carbon Concentration /ppma	≤ 1	FTIR (ASTM F123-91)

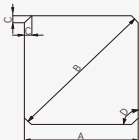
Material properties

Growth method	CZ	/
Crystallinity	Monocrystalline	/
Etch pit density (dislocation density)/pcs/cm ²	≤ 500	Preferential Etch Techniques(ASTM F47-88)
Surface orientation/ $^{\circ}$	$<100>\pm 3$	X-ray Diffraction Method
Orientation of pseudo square sides/ $^{\circ}$	$<010>, <001>\pm 3$	X-ray Diffraction Method

Geometric dimensions and surface properties

Wafer model	M10	/
Geometry	Quasi square	/
Bevel edge shape	Round	/
Wafer Side length/mm	182.2/182.2 $\pm$ 0.25	AOI
Wafer Diameter/mm	247 $\pm$ 0.25	AOI
Arc length projection/mm	7.72 $\pm$ 0.5	AOI
Angle between adjacent sides/ $^{\circ}$	90 $\pm$ 0.15	AOI
Thickness/ μ m	130/135/140 $\pm$ 10	AOI
Batch mean/ μ m	$\geq 130/135/140$	AOI
TTV/ μ m	≤ 25	AOI
Saw Mark/ μ m	≤ 15	AOI
Bow/ μ m	≤ 40	AOI
Warpage/ μ m	≤ 40	AOI
Cutting method	DW	/
Surface quality	No visual defects (no stains, no finger prints, no oil, no glue). No color difference, No bright line	AOI
Chipping	Depth $\leq$ 0.3 mm , Length $\leq$ 0.5 mm; Count $\leq$ 2 /pcs, no V-chip	Naked eyes or wafer inspection system
Micro cracks / holes	None	AOI

Schematic diagram of wafer size



- A.Shape/Size: 182.2 $\pm$ 0.25 mm
- B.Diagonal: 247 $\pm$ 0.25 mm
- C.Corner Length: 7.72 $\pm$ 0.5 mm
- D.Right Angle: 90 $\pm$ 0.15 $^{\circ}$